NSN 5962-01-372-7430

Memory Microcircuit - Page 1 of 2



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Between 1.260 inches and 1.280 inches

Body Width:

Between 0.290 inches and 0.310 inches

Body Height:

Between 0.180 inches and 0.200 inches

Maximum Power Dissipation Rating:

650.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Eo lorops

Features Provided:

Electrostatic sensitive and hermetically sealed and burn in and programmed and w/clock

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

22 input

Criticality Code Justification:

Feat

Case Outline Source And Designator:

D-9 mil-m-38510

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, programmed

Voltage Rating And Type Per Characteristic:

7.0 volts power source

Time Rating Per Chacteristic:

55.00 nanoseconds propagation delay time, low to high level output and 55.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Pal

Special Features:

Electrostatic discharge sensitive; altered item, make from 5962-8686401lx, checksum 0407; nha pn 1372ae1062, 5998-01-358-7044 circuit card assembly

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

NSN 5962-01-372-7430

Memory Microcircuit - Page 2 of 2



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24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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